

Docket No.: M4065.0528/P528-A
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Cem Basceri, et al.

Application No.: Not Yet Assigned

Group Art Unit: 2814

Filed: September 11, 2003

Examiner: N. Ha

For: MIS CAPACITOR AND METHOD OF
FORMATION

FIRST PRELIMINARY AMENDMENT

Box Non-Fee Amendment
Commissioner for Patents
Washington, DC 20231

Dear Sir:

Prior to examination on the merits, please amend the above-identified U.S.
patent application as follows:

In the Specification

Page 2, after the title, please insert --This application is a divisional of Application
Ser. No. 10/145,993, filed May 16, 2002, the disclosure of which is incorporated by
reference herein.--

In the Claims

Please cancel claims 1-64.

Please amend claims 69 and 77-79 as shown.

69. (Amended) The method of claim ~~69~~ 68, wherein said act of etching said layer of hemispherical grained polysilicon further comprises contacting said layer of hemispherical grained polysilicon with a solution of HF.

77. (Amended) The method of claim ~~77~~ 76, wherein said act of providing said boron-doped titanium nitride layer further comprises the act of incorporating boron into a titanium nitride layer.

78. (Amended) The method of claim ~~78~~ 77, wherein said act of incorporating boron into a titanium nitride layer further comprises the act of exposing said titanium nitride layer to B_2H_6 .

79. (Amended) The method of claim ~~79~~ 78, wherein said act of incorporating boron into a titanium nitride layer further comprises the act of exposing said titanium nitride layer to B_2H_6 at a temperature of about $200^{\circ}C$ to about $600^{\circ}C$.